

35th RD50 Workshop (CERN)

Monday, 18 November 2019

Defect Characterization: Defect, Material and Sensor Characterization - 30/7-018 - Kjell Johnsen Auditorium (11:00 - 17:00)

-Conveners: Ioana Pintilie; Eckhart Fretwurst; Michael Moll

time	[id] title	presenter
11:00	[10] Evidence of charge multiplication in silicon detectors operated at a temperature of 1.9 K	SHEPELEV, Artem
11:20	[16] Enhanced influence of defect clusters on the electric field distribution in Si detectors: irradiation with 40Ar ions	Dr EREMIN, Vladimir
11:40	[32] Investigation of the reactor neutron irradiated Si single crystal by a low energy neutron scattering.	VAITKUS, Juozas
12:00	[38] Electron transport via defect network	Prof. ABRAMAVICIUS, Darius
12:20	Lunch Break	
13:30	[28] Defect characterisation after electron irradiation and overview of acceptor removal in Boron doped Si	GURIMSKAYA, Yana
13:50	[3] Low-temperature photoluminescence spectroscopy for LGAD structures	LAUER, Kevin
14:10	[12] Modeling of Defects Properties in Bragg Peak	Ms MITINA, Daria
14:30	[6] Defect investigations of neutron irradiated high resistivity PiN and LGAD diodes	PINTILIE, Ioana
14:50	[13] On the frequency dependence of the admittance of radiation damaged pad diodes	SCHWANDT, Joern
15:10	Another Coffee Break	
15:40	[8] Radiation damage investigation of epitaxial P type Silicon using Schottky diodes and pn junctions	VILLANI, Enrico Giulio
16:00	[36] Discussion Session: Defects	PINTILIE, Ioana